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"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "[Embedded - Microcontrollers](#)"

Details

Product Status	Discontinued at Digi-Key
Core Processor	ARM® Cortex®-M4F
Core Size	32-Bit Single-Core
Speed	48MHz
Connectivity	I ² C, IrDA, SmartCard, SPI, UART/USART
Peripherals	Brown-out Detect/Reset, DMA, I ² S, LCD, POR, PWM, WDT
Number of I/O	56
Program Memory Size	64KB (64K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	32K x 8
Voltage - Supply (Vcc/Vdd)	1.98V ~ 3.8V
Data Converters	A/D 8x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	64-VFQFN Exposed Pad
Supplier Device Package	-
Purchase URL	https://www.e-xfl.com/product-detail/silicon-labs/efm32wg840f64-qfn64t

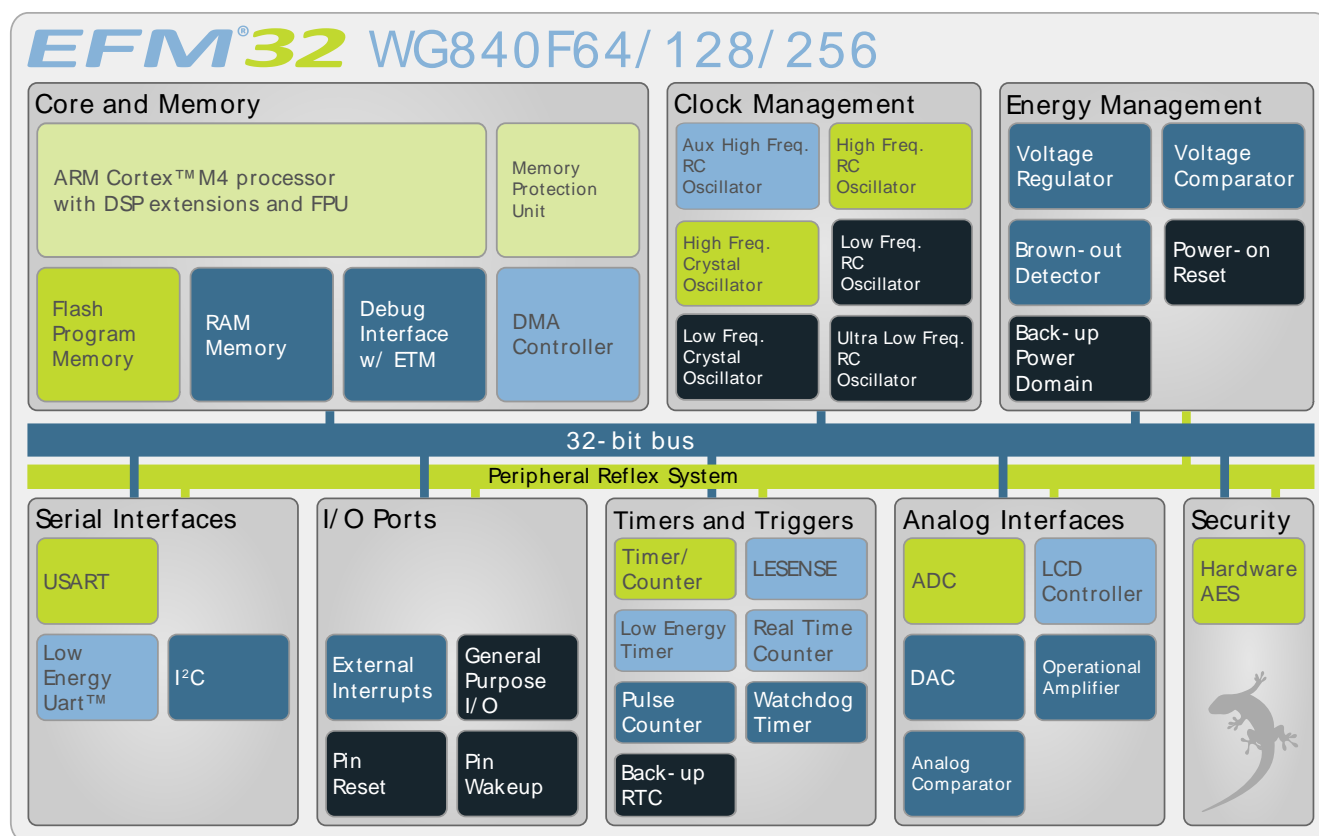
2 System Summary

2.1 System Introduction

The EFM32 MCUs are the world's most energy friendly microcontrollers. With a unique combination of the powerful 32-bit ARM Cortex-M4, with DSP instruction support and floating-point unit, innovative low energy techniques, short wake-up time from energy saving modes, and a wide selection of peripherals, the EFM32WG microcontroller is well suited for any battery operated application as well as other systems requiring high performance and low-energy consumption. This section gives a short introduction to each of the modules in general terms and also shows a summary of the configuration for the EFM32WG840 devices. For a complete feature set and in-depth information on the modules, the reader is referred to the *EFM32WG Reference Manual*.

A block diagram of the EFM32WG840 is shown in Figure 2.1 (p. 3) .

Figure 2.1. Block Diagram



2.1.1 ARM Cortex-M4 Core

The ARM Cortex-M4 includes a 32-bit RISC processor, with DSP instruction support and floating-point unit, which can achieve as much as 1.25 Dhrystone MIPS/MHz. A Memory Protection Unit with support for up to 8 memory segments is included, as well as a Wake-up Interrupt Controller handling interrupts triggered while the CPU is asleep. The EFM32 implementation of the Cortex-M4 is described in detail in *ARM Cortex-M4 Devices Generic User Guide*.

2.1.2 Debug Interface (DBG)

This device includes hardware debug support through a 2-pin serial-wire debug interface and an Embedded Trace Module (ETM) for data/instruction tracing. In addition there is also a 1-wire Serial Wire Viewer pin which can be used to output profiling information, data trace and software-generated messages.

2.1.19 Analog Comparator (ACMP)

The Analog Comparator is used to compare the voltage of two analog inputs, with a digital output indicating which input voltage is higher. Inputs can either be one of the selectable internal references or from external pins. Response time and thereby also the current consumption can be configured by altering the current supply to the comparator.

2.1.20 Voltage Comparator (VCMP)

The Voltage Supply Comparator is used to monitor the supply voltage from software. An interrupt can be generated when the supply falls below or rises above a programmable threshold. Response time and thereby also the current consumption can be configured by altering the current supply to the comparator.

2.1.21 Analog to Digital Converter (ADC)

The ADC is a Successive Approximation Register (SAR) architecture, with a resolution of up to 12 bits at up to one million samples per second. The integrated input mux can select inputs from 8 external pins and 6 internal signals.

2.1.22 Digital to Analog Converter (DAC)

The Digital to Analog Converter (DAC) can convert a digital value to an analog output voltage. The DAC is fully differential rail-to-rail, with 12-bit resolution. It has two single ended output buffers which can be combined into one differential output. The DAC may be used for a number of different applications such as sensor interfaces or sound output.

2.1.23 Operational Amplifier (OPAMP)

The EFM32WG840 features 3 Operational Amplifiers. The Operational Amplifier is a versatile general purpose amplifier with rail-to-rail differential input and rail-to-rail single ended output. The input can be set to pin, DAC or OPAMP, whereas the output can be pin, OPAMP or ADC. The current is programmable and the OPAMP has various internal configurations such as unity gain, programmable gain using internal resistors etc.

2.1.24 Low Energy Sensor Interface (LESENSE)

The Low Energy Sensor Interface (LESENSE[™]), is a highly configurable sensor interface with support for up to 16 individually configurable sensors. By controlling the analog comparators and DAC, LESENSE is capable of supporting a wide range of sensors and measurement schemes, and can for instance measure LC sensors, resistive sensors and capacitive sensors. LESENSE also includes a programmable FSM which enables simple processing of measurement results without CPU intervention. LESENSE is available in energy mode EM2, in addition to EM0 and EM1, making it ideal for sensor monitoring in applications with a strict energy budget.

2.1.25 Backup Power Domain

The backup power domain is a separate power domain containing a Backup Real Time Counter, BURTC, and a set of retention registers, available in all energy modes. This power domain can be configured to automatically change power source to a backup battery when the main power drains out. The backup power domain enables the EFM32WG840 to keep track of time and retain data, even if the main power source should drain out.

2.1.26 Advanced Encryption Standard Accelerator (AES)

The AES accelerator performs AES encryption and decryption with 128-bit or 256-bit keys. Encrypting or decrypting one 128-bit data block takes 52 HFCORECLK cycles with 128-bit keys and 75 HFCORECLK

3 Electrical Characteristics

3.1 Test Conditions

3.1.1 Typical Values

The typical data are based on $T_{AMB}=25^{\circ}\text{C}$ and $V_{DD}=3.0\text{ V}$, as defined in Table 3.2 (p. 10), by simulation and/or technology characterisation unless otherwise specified.

3.1.2 Minimum and Maximum Values

The minimum and maximum values represent the worst conditions of ambient temperature, supply voltage and frequencies, as defined in Table 3.2 (p. 10), by simulation and/or technology characterisation unless otherwise specified.

3.2 Absolute Maximum Ratings

The absolute maximum ratings are stress ratings, and functional operation under such conditions are not guaranteed. Stress beyond the limits specified in Table 3.1 (p. 10) may affect the device reliability or cause permanent damage to the device. Functional operating conditions are given in Table 3.2 (p. 10).

Table 3.1. Absolute Maximum Ratings

Symbol	Parameter	Condition	Min	Typ	Max	Unit
T_{STG}	Storage temperature range		-40		150 ¹	$^{\circ}\text{C}$
T_S	Maximum soldering temperature	Latest IPC/JEDEC J-STD-020 Standard			260	$^{\circ}\text{C}$
V_{DDMAX}	External main supply voltage		0		3.8	V
V_{IOPIN}	Voltage on any I/O pin		-0.3		$V_{DD}+0.3$	V

¹Based on programmed devices tested for 10000 hours at 150°C . Storage temperature affects retention of preprogrammed calibration values stored in flash. Please refer to the Flash section in the Electrical Characteristics for information on flash data retention for different temperatures.

3.3 General Operating Conditions

3.3.1 General Operating Conditions

Table 3.2. General Operating Conditions

Symbol	Parameter	Min	Typ	Max	Unit
T_{AMB}	Ambient temperature range	-40		85	$^{\circ}\text{C}$
V_{DDOP}	Operating supply voltage	1.98		3.8	V
f_{APB}	Internal APB clock frequency			48	MHz
f_{AHB}	Internal AHB clock frequency			48	MHz

Figure 3.3. EM1 Current consumption with all peripheral clocks disabled and HFRCO running at 21MHz

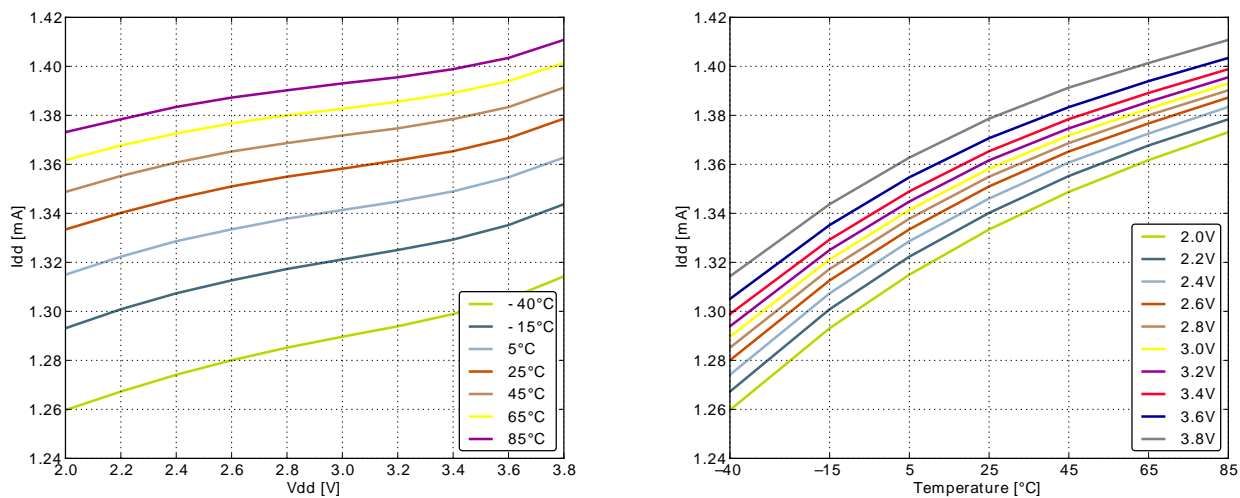
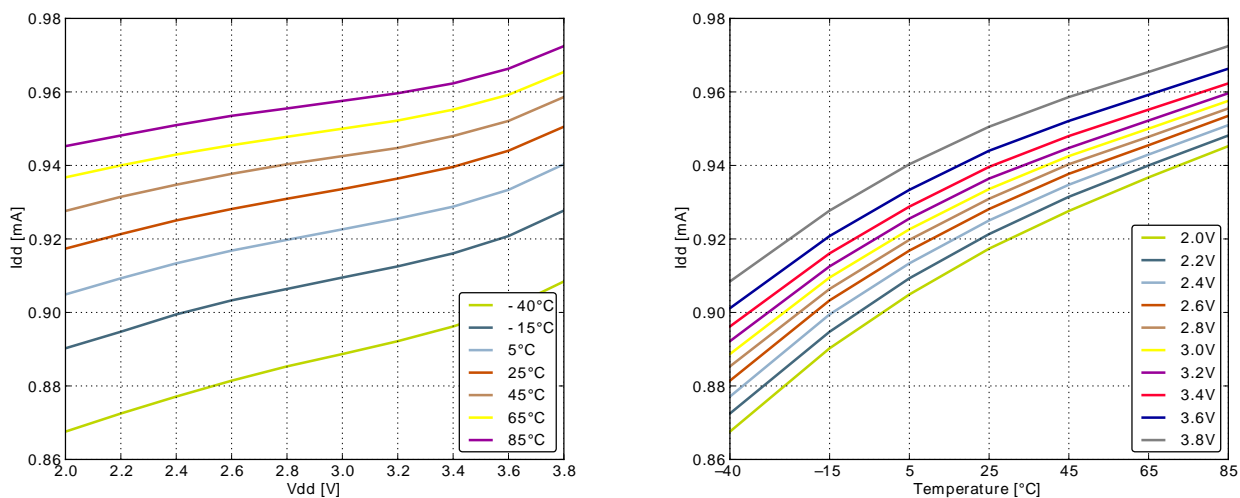
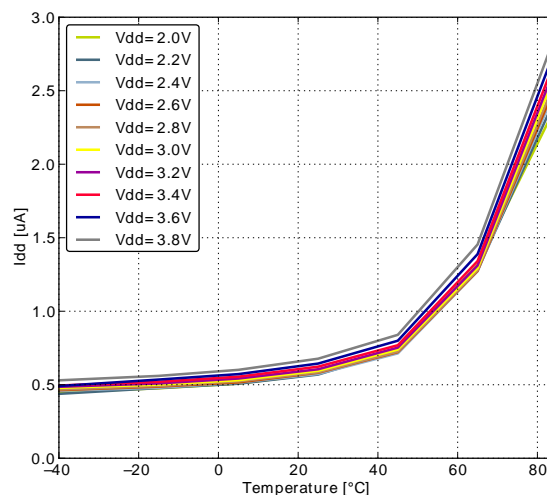
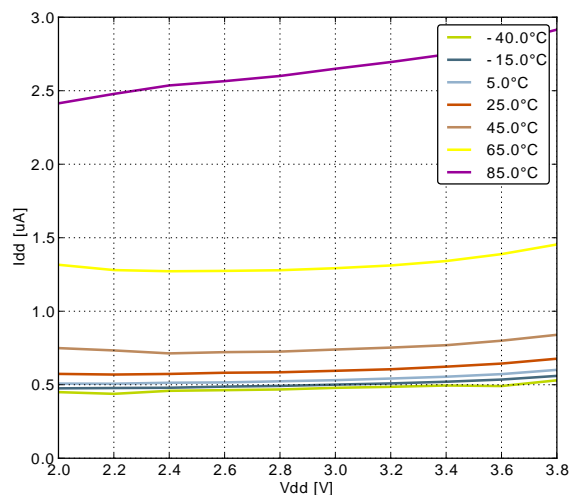


Figure 3.4. EM1 Current consumption with all peripheral clocks disabled and HFRCO running at 14MHz



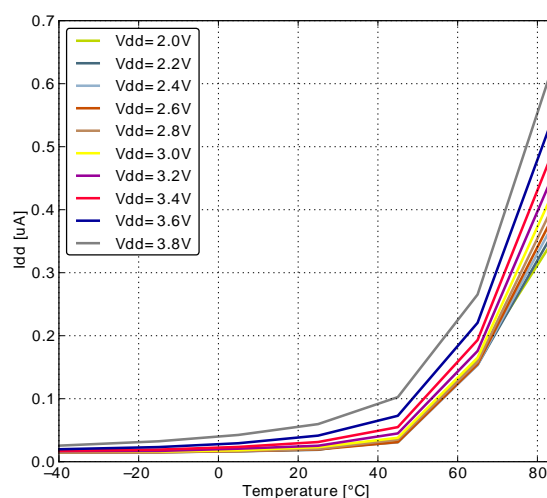
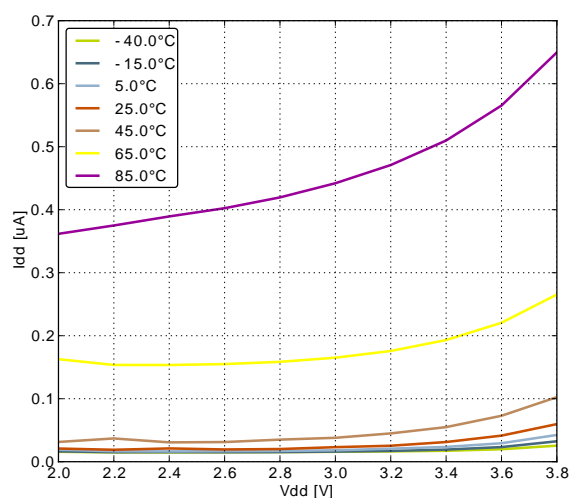
3.4.3 EM3 Current Consumption

Figure 3.9. EM3 current consumption.



3.4.4 EM4 Current Consumption

Figure 3.10. EM4 current consumption.



3.5 Transition between Energy Modes

The transition times are measured from the trigger to the first clock edge in the CPU.

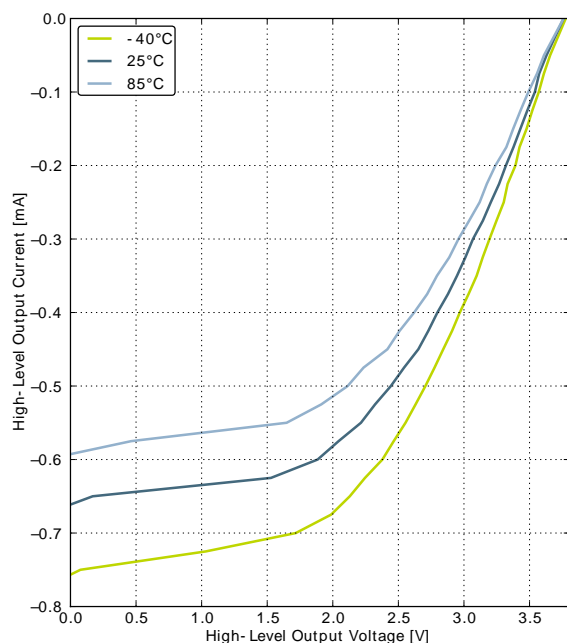
Table 3.5. Energy Modes Transitions

Symbol	Parameter	Min	Typ	Max	Unit
t_{EM10}	Transition time from EM1 to EM0		0		HF-CORE-CLK cycles
t_{EM20}	Transition time from EM2 to EM0		2		μs
t_{EM30}	Transition time from EM3 to EM0		2		μs
t_{EM40}	Transition time from EM4 to EM0		163		μs

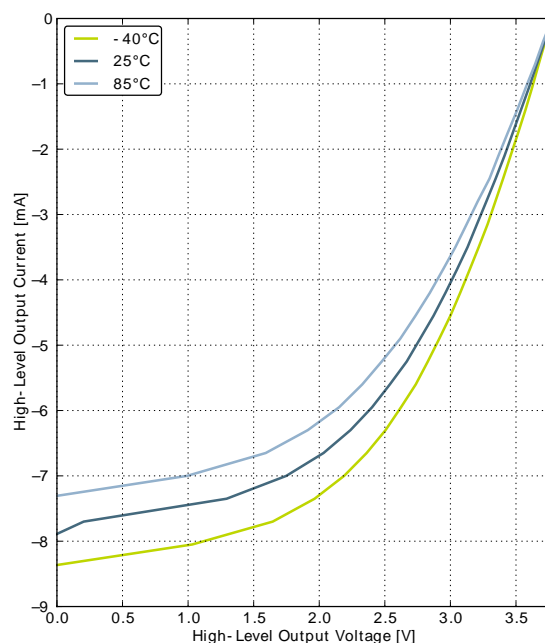
3.8 General Purpose Input Output

Table 3.8. GPIO

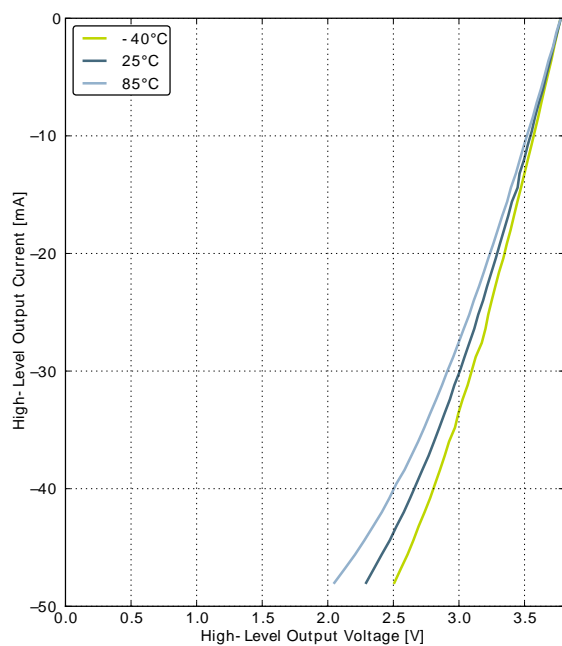
Symbol	Parameter	Condition	Min	Typ	Max	Unit
V _{IOIL}	Input low voltage				0.30V _{DD}	V
V _{IOIH}	Input high voltage		0.70V _{DD}			V
V _{IOOH}	Output high voltage (Production test condition = 3.0V, DRIVEMODE = STANDARD)	Sourcing 0.1 mA, V _{DD} =1.98 V, GPIO_Px_CTRL DRIVEMODE = LOWEST		0.80V _{DD}		V
		Sourcing 0.1 mA, V _{DD} =3.0 V, GPIO_Px_CTRL DRIVEMODE = LOWEST		0.90V _{DD}		V
		Sourcing 1 mA, V _{DD} =1.98 V, GPIO_Px_CTRL DRIVEMODE = LOW		0.85V _{DD}		V
		Sourcing 1 mA, V _{DD} =3.0 V, GPIO_Px_CTRL DRIVEMODE = LOW		0.90V _{DD}		V
		Sourcing 6 mA, V _{DD} =1.98 V, GPIO_Px_CTRL DRIVEMODE = STANDARD	0.75V _{DD}			V
		Sourcing 6 mA, V _{DD} =3.0 V, GPIO_Px_CTRL DRIVEMODE = STANDARD	0.85V _{DD}			V
		Sourcing 20 mA, V _{DD} =1.98 V, GPIO_Px_CTRL DRIVEMODE = HIGH	0.60V _{DD}			V
		Sourcing 20 mA, V _{DD} =3.0 V, GPIO_Px_CTRL DRIVEMODE = HIGH	0.80V _{DD}			V
V _{IOOL}	Output low voltage (Production test condition = 3.0V, DRIVEMODE = STANDARD)	Sinking 0.1 mA, V _{DD} =1.98 V, GPIO_Px_CTRL DRIVEMODE = LOWEST		0.20V _{DD}		V
		Sinking 0.1 mA, V _{DD} =3.0 V, GPIO_Px_CTRL DRIVEMODE = LOWEST		0.10V _{DD}		V
		Sinking 1 mA, V _{DD} =1.98 V, GPIO_Px_CTRL DRIVEMODE = LOW		0.10V _{DD}		V
		Sinking 1 mA, V _{DD} =3.0 V, GPIO_Px_CTRL DRIVEMODE = LOW		0.05V _{DD}		V
		Sinking 6 mA, V _{DD} =1.98 V, GPIO_Px_CTRL DRIVEMODE = STANDARD			0.30V _{DD}	V
		Sinking 6 mA, V _{DD} =3.0 V, GPIO_Px_CTRL DRIVEMODE = STANDARD			0.20V _{DD}	V
		Sinking 20 mA, V _{DD} =1.98 V, GPIO_Px_CTRL DRIVEMODE = HIGH			0.35V _{DD}	V

Figure 3.16. Typical High-Level Output Current, 3.8V Supply Voltage

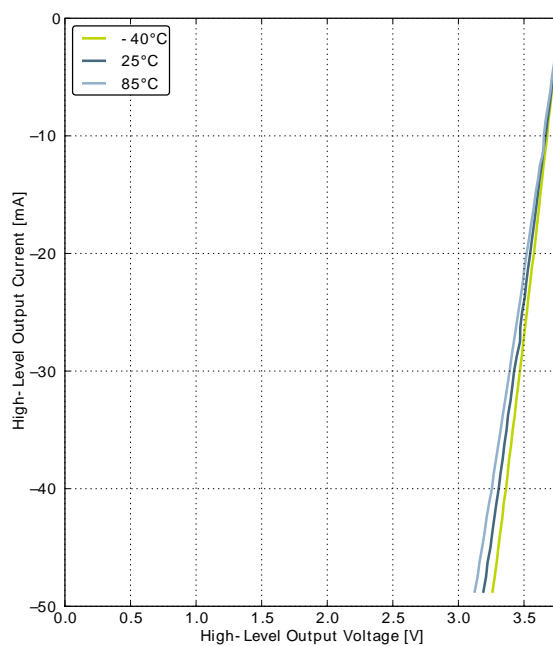
GPIO_Px_CTRL DRIVEMODE = LOWEST



GPIO_Px_CTRL DRIVEMODE = LOW



GPIO_Px_CTRL DRIVEMODE = STANDARD



GPIO_Px_CTRL DRIVEMODE = HIGH

3.9.3 LFRCO

Table 3.11. LFRCO

Symbol	Parameter	Condition	Min	Typ	Max	Unit
f_{LFRCO}	Oscillation frequency, $V_{\text{DD}} = 3.0 \text{ V}$, $T_{\text{AMB}} = 25^\circ\text{C}$		31.29	32.768	34.28	kHz
t_{LFRCO}	Startup time not including software calibration			150		μs
I_{LFRCO}	Current consumption			300		nA
TUNESTEP _{LFRCO}	Frequency step for LSB change in TUNING value			1.5		%

Figure 3.17. Calibrated LFRCO Frequency vs Temperature and Supply Voltage

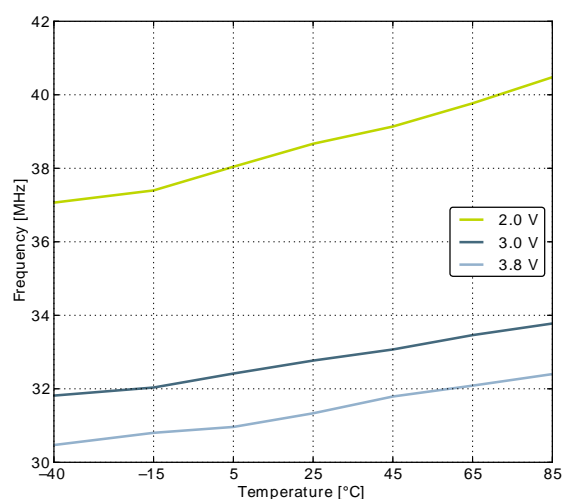
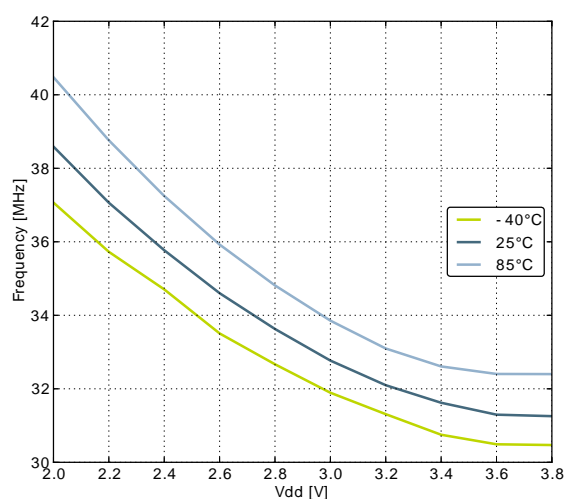
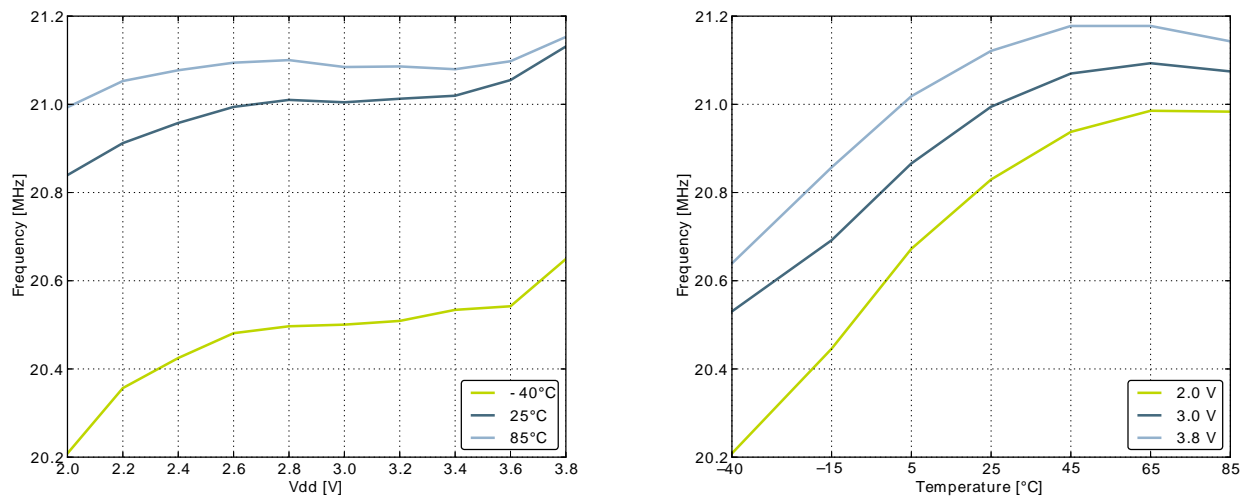
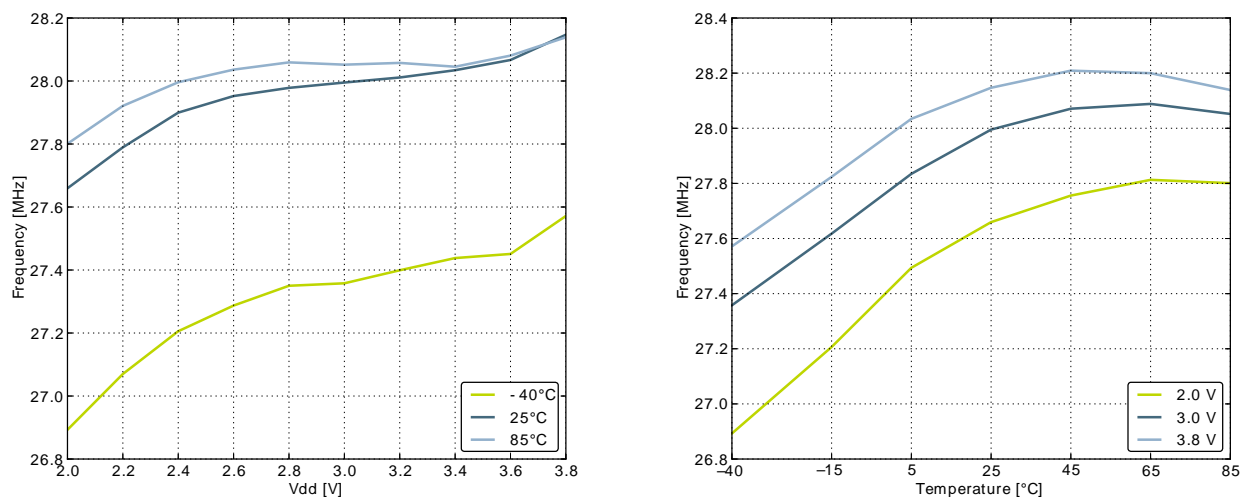
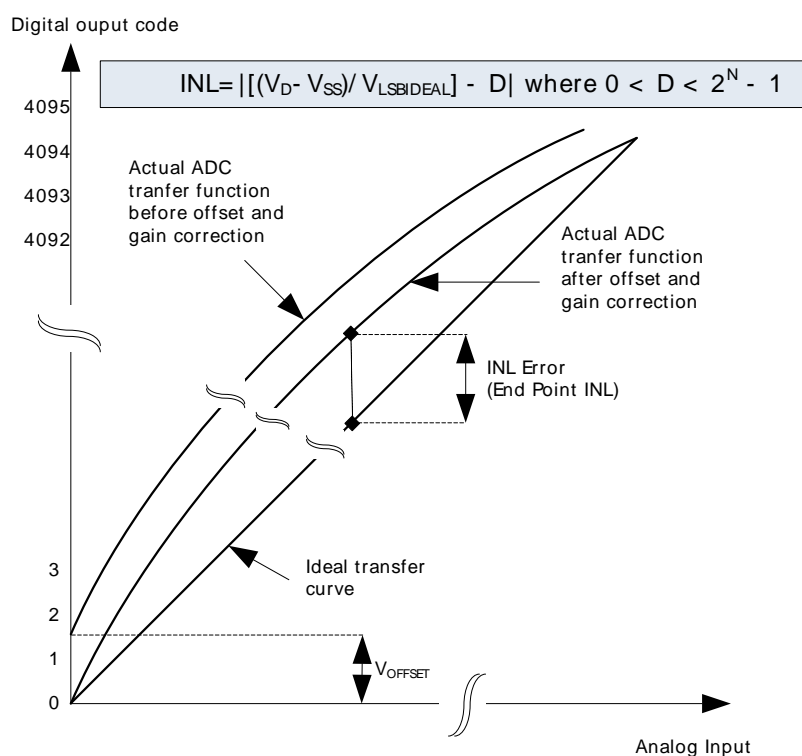
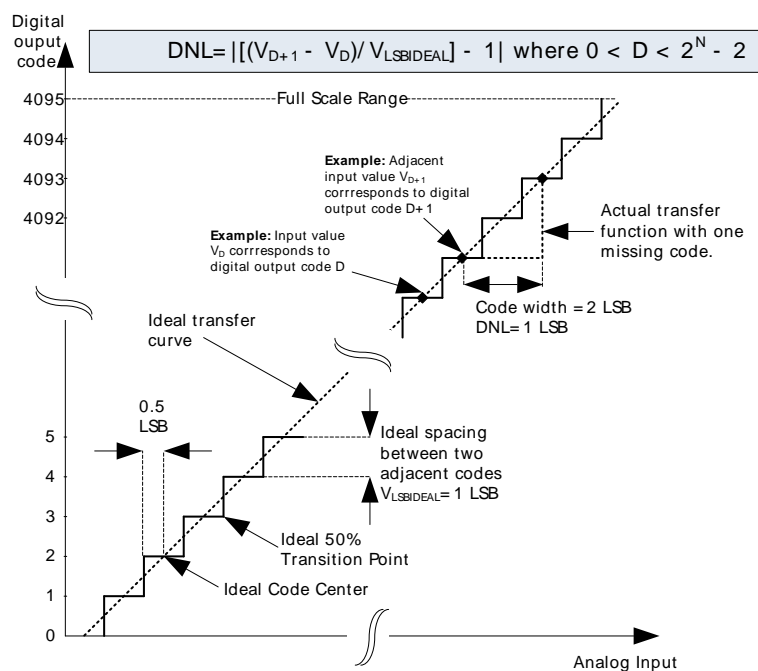


Figure 3.22. Calibrated HFRCO 21 MHz Band Frequency vs Supply Voltage and Temperature**Figure 3.23. Calibrated HFRCO 28 MHz Band Frequency vs Supply Voltage and Temperature**

Symbol	Parameter	Condition	Min	Typ	Max	Unit
	reference voltage on channel 6					
V _{ADCCMIN}	Common mode input range		0		V _{DD}	V
I _{ADCIN}	Input current	2pF sampling capacitors		<100		nA
CMRR _{ADC}	Analog input common mode rejection ratio			65		dB
I _{ADC}	Average active current	1 MSamples/s, 12 bit, external reference		351		μA
		10 kSamples/s 12 bit, internal 1.25 V reference, WARMUP-MODE in ADCn_CTRL set to 0b00		67		μA
		10 kSamples/s 12 bit, internal 1.25 V reference, WARMUP-MODE in ADCn_CTRL set to 0b01		63		μA
		10 kSamples/s 12 bit, internal 1.25 V reference, WARMUP-MODE in ADCn_CTRL set to 0b10		64		μA
I _{ADCREF}	Current consumption of internal voltage reference	Internal voltage reference		65		μA
C _{ADCIN}	Input capacitance			2		pF
R _{ADCIN}	Input ON resistance		1			MΩ
R _{ADCFLT}	Input RC filter resistance			10		kΩ
C _{ADCFLT}	Input RC filter/decoupling capacitance			250		fF
f _{ADCCLK}	ADC Clock Frequency				13	MHz
t _{ADCCONV}	Conversion time	6 bit	7			ADC-CLK Cycles
		8 bit	11			ADC-CLK Cycles
		12 bit	13			ADC-CLK Cycles
t _{ADCACQ}	Acquisition time	Programmable	1		256	ADC-CLK Cycles
t _{ADCACQVDD3}	Required acquisition time for VDD/3 reference		2			μs
t _{ADCSTART}	Startup time of reference generator			5		μs

Figure 3.24. Integral Non-Linearity (INL)**Figure 3.25. Differential Non-Linearity (DNL)**

Symbol	Parameter	Condition	Min	Typ	Max	Unit
		$V_{out}=1V$, RESSEL=0, 0.1 Hz<f<1 MHz, OPAXHCMDIS=0		196		μV_{RMS}
		$V_{out}=1V$, RESSEL=0, 0.1 Hz<f<1 MHz, OPAXHCMDIS=1		229		μV_{RMS}
		RESSEL=7, 0.1 Hz<f<10 kHz, OPAXHCMDIS=0		1230		μV_{RMS}
		RESSEL=7, 0.1 Hz<f<10 kHz, OPAXHCMDIS=1		2130		μV_{RMS}
		RESSEL=7, 0.1 Hz<f<1 MHz, OPAXHCMDIS=0		1630		μV_{RMS}
		RESSEL=7, 0.1 Hz<f<1 MHz, OPAXHCMDIS=1		2590		μV_{RMS}

Figure 3.32. OPAMP Common Mode Rejection Ratio

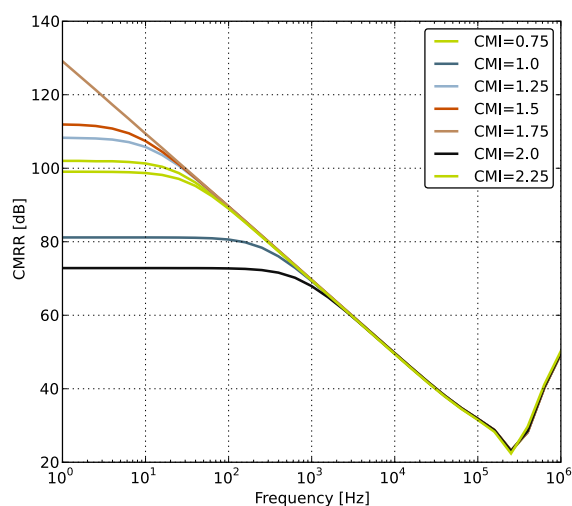


Figure 3.33. OPAMP Positive Power Supply Rejection Ratio

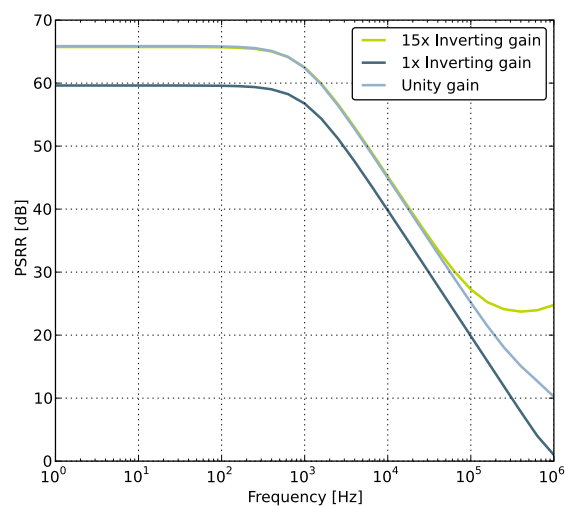


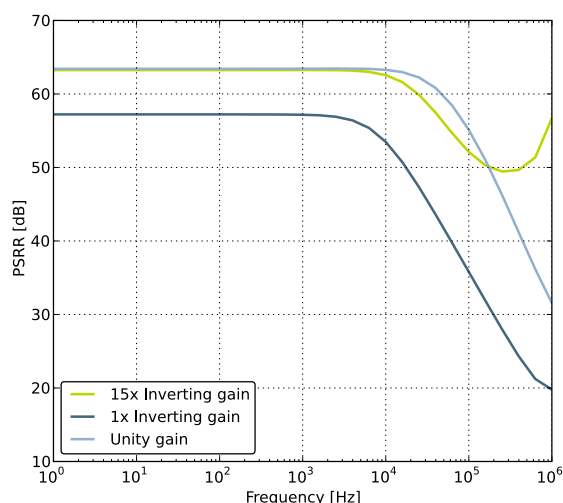
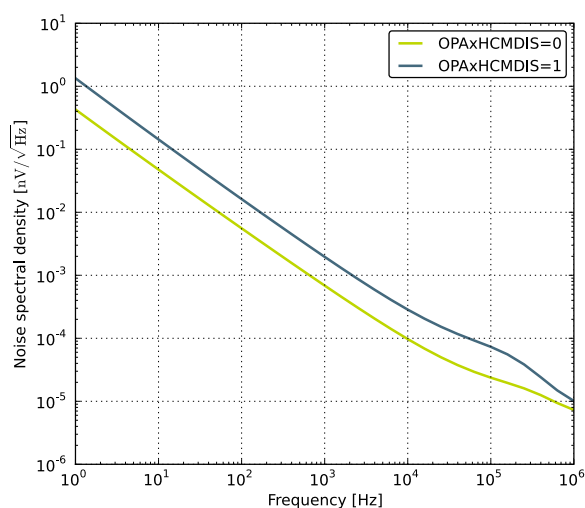
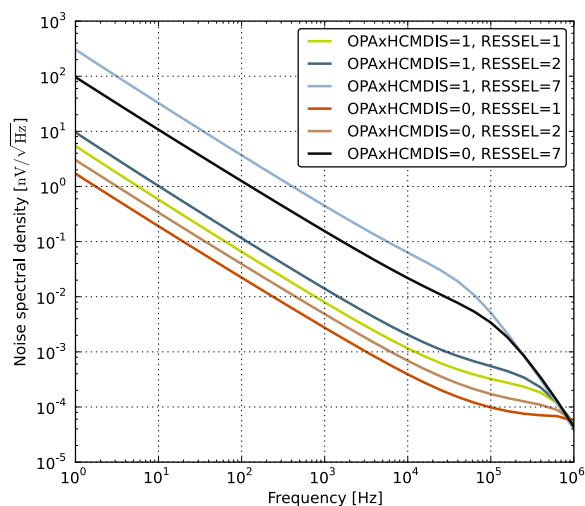
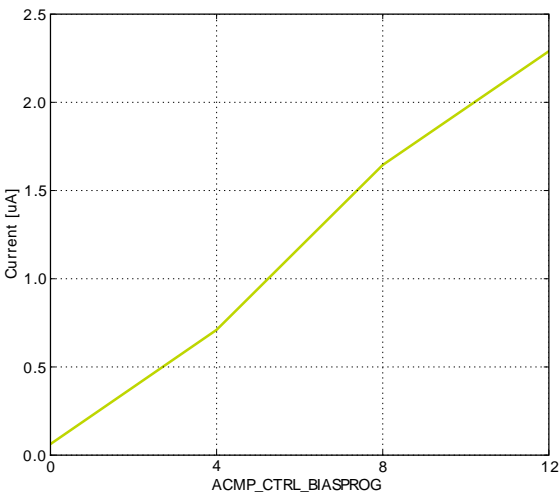
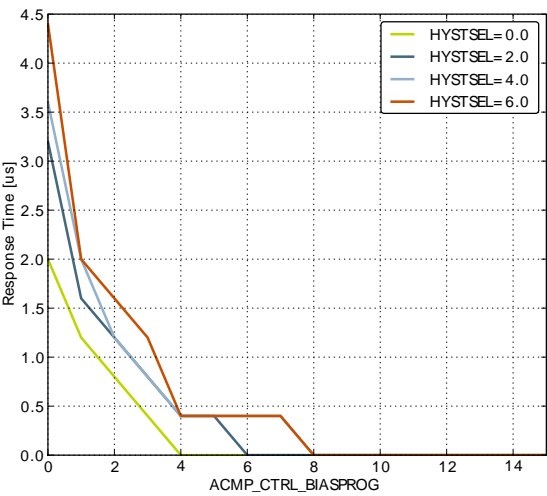
Figure 3.34. OPAMP Negative Power Supply Rejection Ratio**Figure 3.35. OPAMP Voltage Noise Spectral Density (Unity Gain) $V_{out}=1V$** **Figure 3.36. OPAMP Voltage Noise Spectral Density (Non-Unity Gain)**

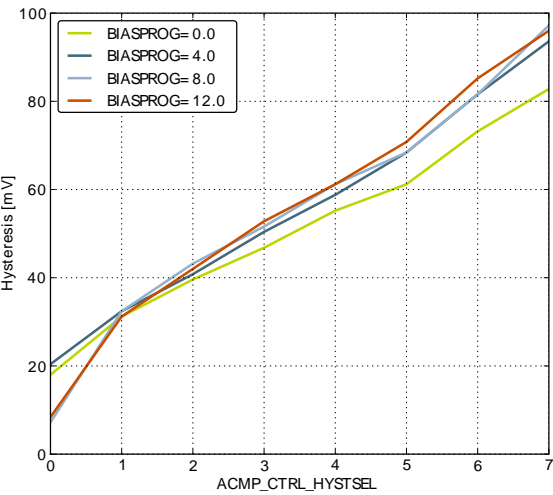
Figure 3.37. ACMP Characteristics, Vdd = 3V, Temp = 25°C, FULLBIAS = 0, HALFBIAS = 1



Current consumption, HYSTSEL = 4



Response time



Hysteresis

3.15 LCD

Table 3.20. LCD

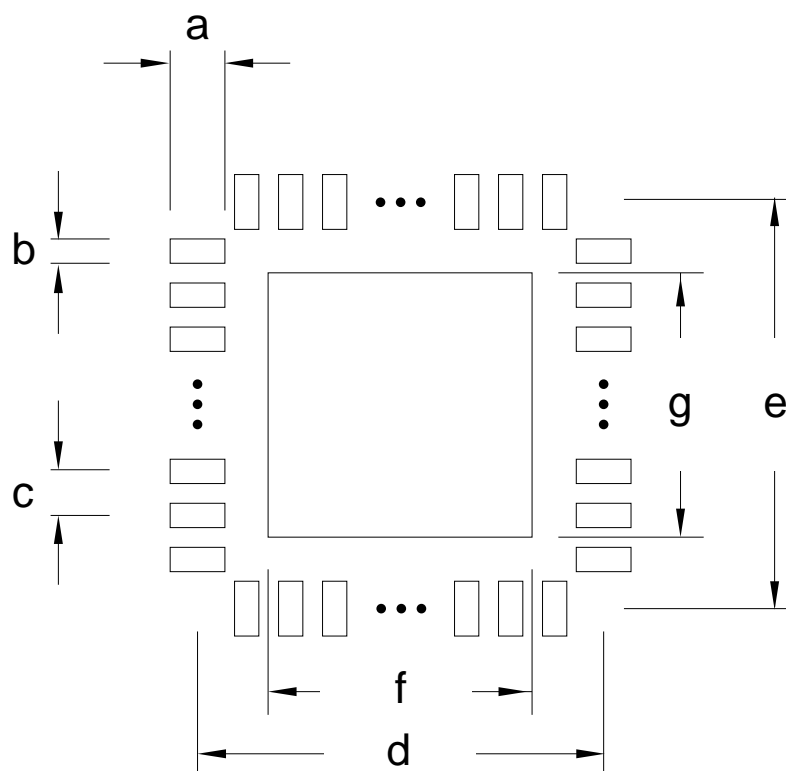
Symbol	Parameter	Condition	Min	Typ	Max	Unit
f_{LCDFR}	Frame rate		30		200	Hz
NUM_{SEG}	Number of segments supported			20x8		seg
V_{LCD}	LCD supply voltage range	Internal boost circuit enabled	2.0		3.8	V
I_{LCD}	Steady state current consumption.	Display disconnected, static mode, framerate 32 Hz, all segments on.		250		nA
		Display disconnected, quadruplex mode, framerate 32 Hz, all segments on, bias mode to ONETHIRD in LCD_DISPCTRL register.		550		nA
I_{LCDBOOST}	Steady state Current contribution of internal boost.	Internal voltage boost off		0		μA
		Internal voltage boost on, boosting from 2.2 V to 3.0 V.		8.4		μA
V_{BOOST}	Boost Voltage	VBLEV of LCD_DISPCTRL register to LEVEL0		3.02		V
		VBLEV of LCD_DISPCTRL register to LEVEL1		3.15		V
		VBLEV of LCD_DISPCTRL register to LEVEL2		3.28		V
		VBLEV of LCD_DISPCTRL register to LEVEL3		3.41		V
		VBLEV of LCD_DISPCTRL register to LEVEL4		3.54		V
		VBLEV of LCD_DISPCTRL register to LEVEL5		3.67		V
		VBLEV of LCD_DISPCTRL register to LEVEL6		3.73		V
		VBLEV of LCD_DISPCTRL register to LEVEL7		3.74		V

The total LCD current is given by Equation 3.3 (p. 50) . I_{LCDBOOST} is zero if internal boost is off.

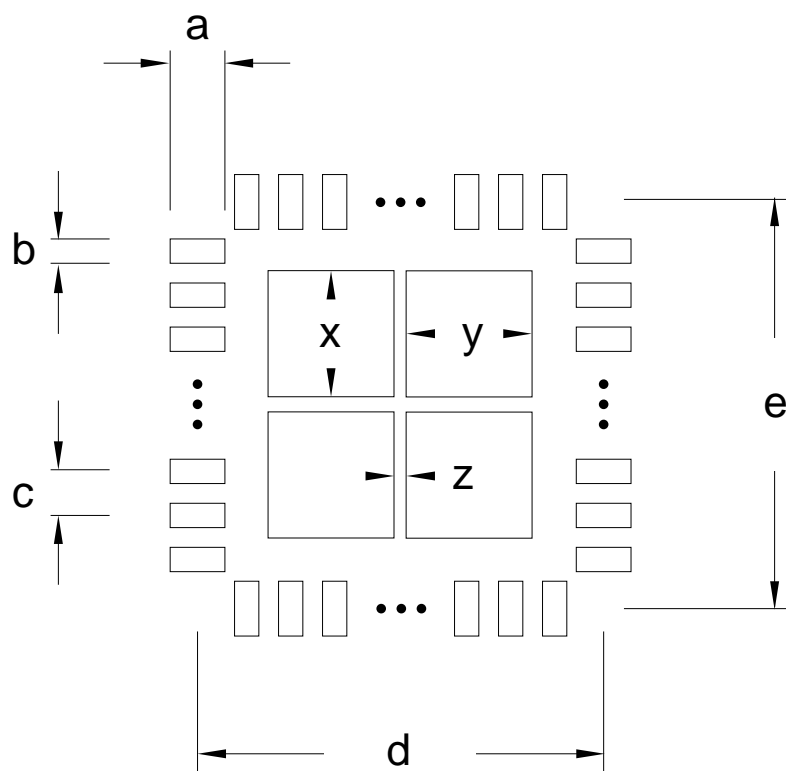
Total LCD Current Based on Operational Mode and Internal Boost

$$I_{\text{LCDTOTAL}} = I_{\text{LCD}} + I_{\text{LCDBOOST}} \quad (3.3)$$

QFN64 Pin# and Name		Pin Alternate Functionality / Description			
Pin #	Pin Name	Analog	Timers	Communication	Other
		OPAMP_OUT1ALT			
30	PD2	ADC0_CH2	TIM0_CC1 #3	US1_CLK #1	DBG_SWO #3
31	PD3	ADC0_CH3 OPAMP_N2	TIM0_CC2 #3	US1_CS #1	ETM_TD1 #0/2
32	PD4	ADC0_CH4 OPAMP_P2		LEU0_TX #0	ETM_TD2 #0/2
33	PD5	ADC0_CH5 OPAMP_OUT2 #0		LEU0_RX #0	ETM_TD3 #0/2
34	PD6	ADC0_CH6 DAC0_P1 / OPAMP_P1	TIM1_CC0 #4 LETIM0_OUT0 #0 PCNT0_S0IN #3	US1_RX #2 I2C0_SDA #1	LES_ALTEX0 #0 ACMP0_O #2 ETM_TD0 #0
35	PD7	ADC0_CH7 DAC0_N1 / OPAMP_N1	TIM1_CC1 #4 LETIM0_OUT1 #0 PCNT0_S1IN #3	US1_TX #2 I2C0_SCL #1	CMU_CLK0 #2 LES_ALTEX1 #0 ACMP1_O #2 ETM_TCLK #0
36	PD8	BU_VIN			CMU_CLK1 #1
37	PC6	ACMP0_CH6		LEU1_TX #0 I2C0_SDA #2	LES_CH6 #0 ETM_TCLK #2
38	PC7	ACMP0_CH7		LEU1_RX #0 I2C0_SCL #2	LES_CH7 #0 ETM_TD0 #2
39	VDD_DREG	Power supply for on-chip voltage regulator.			
40	DECOUPLE	Decouple output for on-chip voltage regulator. An external capacitance of size C _{DECOUPLE} is required at this pin.			
41	PE4	LCD_COM0		US0_CS #1	
42	PE5	LCD_COM1		US0_CLK #1	
43	PE6	LCD_COM2		US0_RX #1	
44	PE7	LCD_COM3		US0_TX #1	
45	PC12	ACMP1_CH4 DAC0_OUT1ALT #0/ OPAMP_OUT1ALT			CMU_CLK0 #1 LES_CH12 #0
46	PC13	ACMP1_CH5 DAC0_OUT1ALT #1/ OPAMP_OUT1ALT	TIM0_CDTI0 #1/3 TIM1_CC0 #0 TIM1_CC2 #4 PCNT0_S0IN #0		LES_CH13 #0
47	PC14	ACMP1_CH6 DAC0_OUT1ALT #2/ OPAMP_OUT1ALT	TIM0_CDTI1 #1/3 TIM1_CC1 #0 PCNT0_S1IN #0	US0_CS #3	LES_CH14 #0
48	PC15	ACMP1_CH7 DAC0_OUT1ALT #3/ OPAMP_OUT1ALT	TIM0_CDTI2 #1/3 TIM1_CC2 #0	US0_CLK #3	LES_CH15 #0 DBG_SWO #1
49	PF0		TIM0_CC0 #5 LETIM0_OUT0 #2	US1_CLK #2 LEU0_TX #3 I2C0_SDA #5	DBG_SWCLK #0/1/2/3
50	PF1		TIM0_CC1 #5 LETIM0_OUT1 #2	US1_CS #2 LEU0_RX #3 I2C0_SCL #5	DBG_SWDIO #0/1/2/3 GPIO_EM4WU3
51	PF2	LCD_SEG0	TIM0_CC2 #5	LEU0_TX #4	ACMP1_O #0 DBG_SWO #0 GPIO_EM4WU4
52	PF3	LCD_SEG1	TIM0_CDTI0 #2/5		PRS_CH0 #1 ETM_TD3 #1
53	PF4	LCD_SEG2	TIM0_CDTI1 #2/5		PRS_CH1 #1
54	PF5	LCD_SEG3	TIM0_CDTI2 #2/5		PRS_CH2 #1

Figure 5.2. QFN64 PCB Solder Mask**Table 5.2. QFN64 PCB Solder Mask Dimensions (Dimensions in mm)**

Symbol	Dim. (mm)	Symbol	Dim. (mm)
a	0.97	e	8.90
b	0.42	f	7.32
c	0.50	g	7.32
d	8.90	-	-

Figure 5.3. QFN64 PCB Stencil Design**Table 5.3. QFN64 PCB Stencil Design Dimensions (Dimensions in mm)**

Symbol	Dim. (mm)	Symbol	Dim. (mm)
a	0.75	e	8.90
b	0.22	x	2.70
c	0.50	y	2.70
d	8.90	z	0.80

1. The drawings are not to scale.
2. All dimensions are in millimeters.
3. All drawings are subject to change without notice.
4. The PCB Land Pattern drawing is in compliance with IPC-7351B.
5. Stencil thickness 0.125 mm.
6. For detailed pin-positioning, see Figure 4.3 (p. 64) .

5.2 Soldering Information

The latest IPC/JEDEC J-STD-020 recommendations for Pb-Free reflow soldering should be followed.

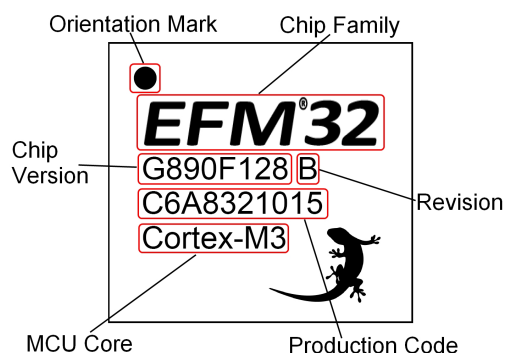
The packages have a Moisture Sensitivity Level rating of 3, please see the latest IPC/JEDEC J-STD-033 standard for MSL description and level 3 bake conditions. Place as many and as small as possible vias underneath each of the solder patches under the ground pad.

6 Chip Marking, Revision and Errata

6.1 Chip Marking

In the illustration below package fields and position are shown.

Figure 6.1. Example Chip Marking (top view)



6.2 Revision

The revision of a chip can be determined from the "Revision" field in Figure 6.1 (p. 68) .

6.3 Errata

Please see the errata document for EFM32WG840 for description and resolution of device erratas. This document is available in Simplicity Studio and online at:

<http://www.silabs.com/support/pages/document-library.aspx?p=MCUs--32-bit>

Removed UART mentioned incorrectly in the QFN64 parts.

Updated Environmental information.

Updated trademark, disclaimer and contact information.

Other minor corrections.

7.4 Revision 1.20

June 28th, 2013

Updated power requirements in the Power Management section.

Removed minimum load capacitance figure and table. Added reference to application note.

Other minor corrections.

7.5 Revision 1.10

May 6th, 2013

Updated current consumption table and figures in Electrical characteristics section.

Other minor corrections.

7.6 Revision 1.00

September 11th, 2012

Updated the HFRCO 1 MHz band typical value to 1.2 MHz.

Updated the HFRCO 7 MHz band typical value to 6.6 MHz.

Other minor corrections.

7.7 Revision 0.95

May 3rd, 2012

Updated EM2/EM3 current consumption at 85°C.

7.8 Revision 0.90

February 27th, 2012

Initial preliminary release.